TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1452A

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

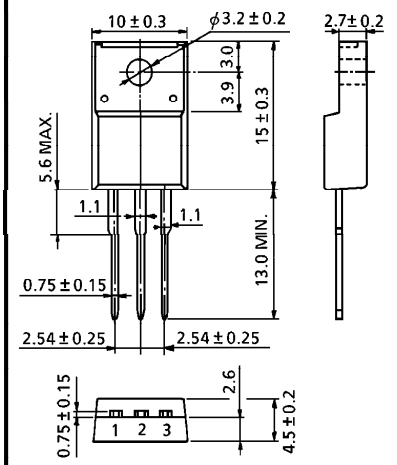
INDUSTRIAL APPLICATIONS

- Low Collector Saturation Voltage
  : $V_{CE\ (sat)} = -0.4V$ (Max.) (at $I_C = -6A$)
- High Speed Switching Time : $t_{stg} = 1.0\mu s$ (Typ.)
- Complementary to 2SC3710A

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−80	V
Collector-Emitter Voltage	V_{CEO}	−80	V
Emitter-Base Voltage	V_{EBO}	−6	V
Collector Current	I_C	−12	A
Base Current	I_B	−2	A
Collector Power Dissipation (Tc = 25°C)	P_C	30	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

Unit in mm



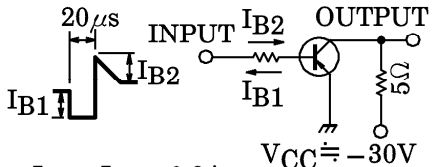
1. BASE
2. COLLECTOR
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-10R1A

961001EAA1

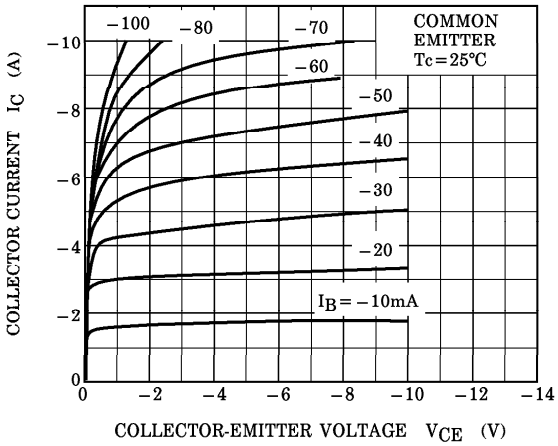
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

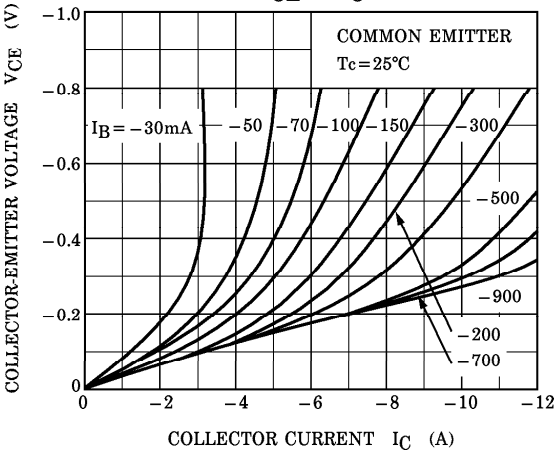
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=-80V$, $I_E=0$	—	—	−10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=-6V$, $I_C=0$		—	−10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)\,CEO}$	$I_C=-50mA$, $I_B=0$	−80	—	—	V
DC Current Gain		$h_{FE\,(1)}$ (Note)	$V_{CE}=-1V$, $I_C=-1A$	70	—	240	
		$h_{FE\,(2)}$	$V_{CE}=-1V$, $I_C=-6A$	40	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE\,(sat)}$	$I_C=-6A$, $I_B=-0.3A$	—	−0.2	−0.4	V
	Base-Emitter	$V_{BE\,(sat)}$	$I_C=-6A$, $I_B=-0.3A$	—	−0.9	−1.2	
Transition Frequency		f_T	$V_{CE}=-5V$, $I_C=-1A$	—	50	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB}=-10V$, $I_E=0$, f=1MHz	—	400	—	pF
Switching Time	Turn-on Time	t_{on}	 $-I_{B1}=I_{B2}=0.3A$ DUTY CYCLE≦1%	—	0.3	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	0.5	—	

Note : $h_{FE\,(1)}$ Classification O : 70~140, Y : 120~240

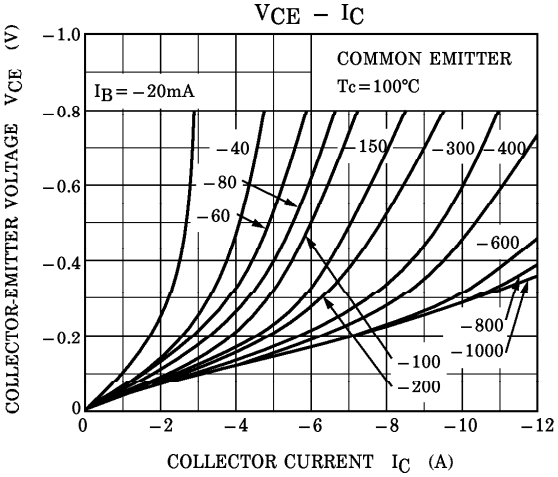
I_C – V_{CE}



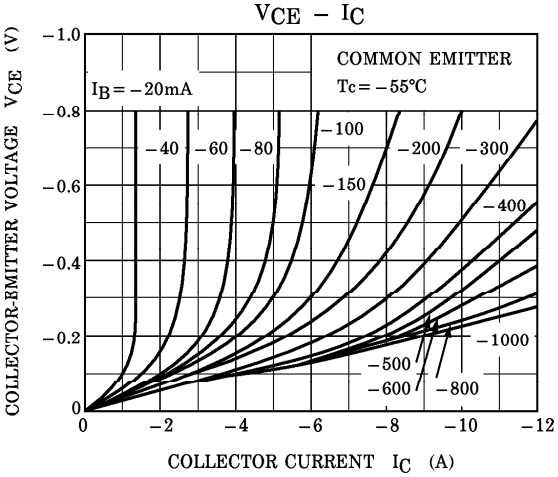
V_{CE} – I_C



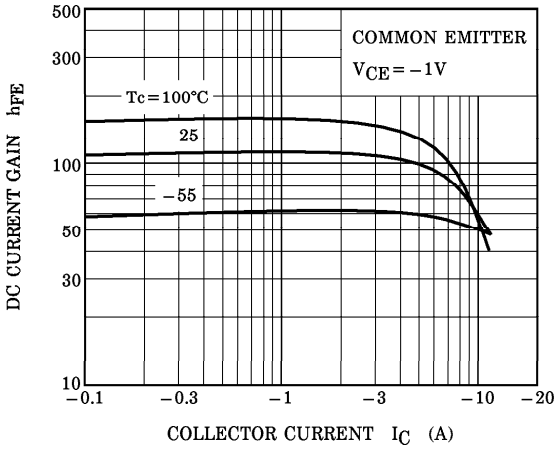
V_{CE} – I_C



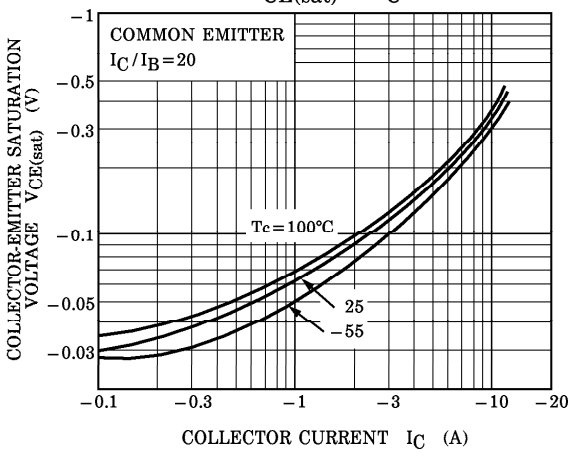
V_{CE} – I_C



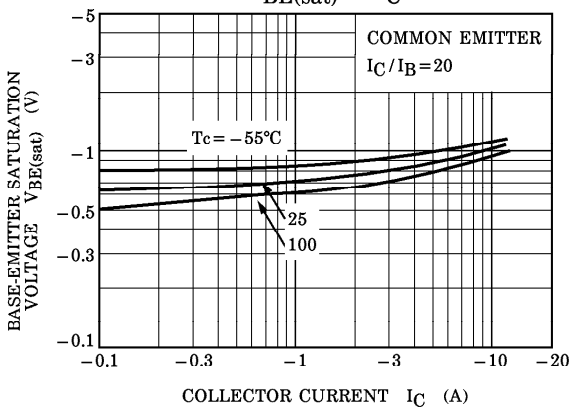
h_{FE} – I_C



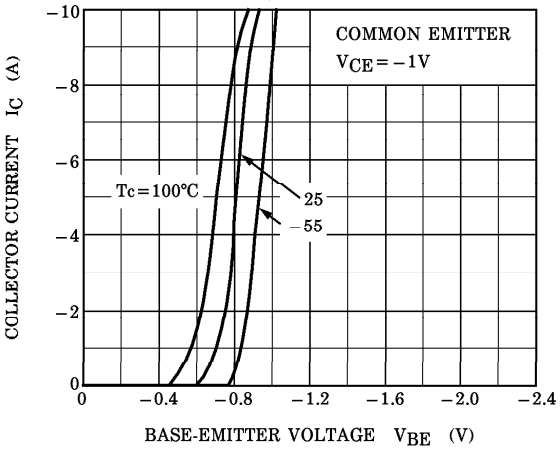
$V_{CE(sat)}$ – I_C



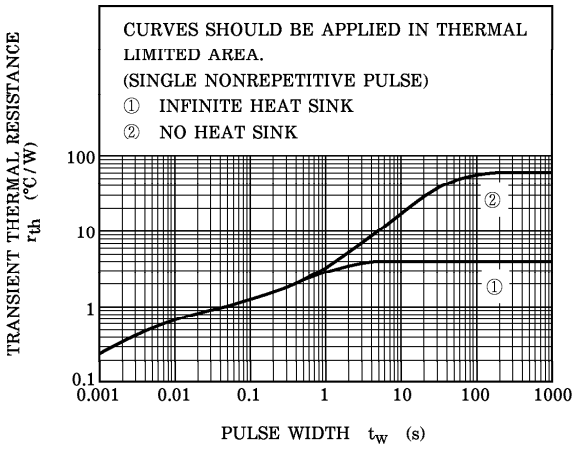
$V_{BE(sat)}$ – I_C



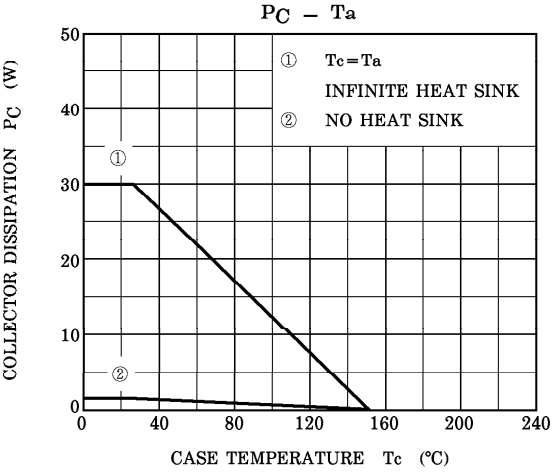
I_C – V_{BE}



r_{th} – t_w



P_C – T_a



SAFE OPERATING AREA

